

RF Power Field Effect Transistors

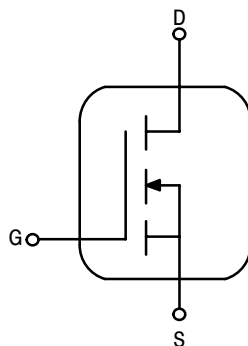
N-Channel Enhancement-Mode Lateral MOSFETs

Designed for broadband commercial and industrial applications with frequencies from 470 to 860 MHz. The high gain and broadband performance of these devices make them ideal for large-signal, common source amplifier applications in 28/32 volt transmitter equipment.

- Typical CW Performance at 860 MHz, 32 Volts, Narrowband Fixture
Output Power — 75 Watts
Power Gain — 18.2 dB
Efficiency — 60%
- Capable of Handling 10:1 VSWR @ 32 Vdc, 860 MHz,
75 Watts CW Output Power

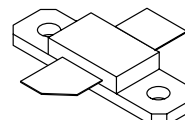
Features

- Integrated ESD Protection
- Excellent Thermal Stability
- Characterized with Series Equivalent Large-Signal Impedance Parameters
- Low Gold Plating Thickness on Leads. L Suffix Indicates 40μ" Nominal.
- RoHS Compliant
- In Tape and Reel. R1 = 500 units per 32 mm, 13 inch Reel.

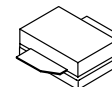


MRF373ALR1
MRF373ALSR1

470-860 MHz, 75 W, 32 V
LATERAL N-CHANNEL
BROADBAND
RF POWER MOSFETs



CASE 360B-05, STYLE 1
NI-360
MRF373ALR1



CASE 360C-05, STYLE 1
NI-360S
MRF373ALSR1

Table 1. Maximum Ratings

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	-0.5, +70	Vdc
Gate-Source Voltage	V_{GS}	-0.5, +15	Vdc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	MRF373ALR1 P_D	197 1.12	W W/°C
	MRF373ALSR1	278 1.59	W W/°C
Storage Temperature Range	T_{stg}	-65 to +150	°C
Case Operating Temperature	T_C	150	°C
Operating Junction Temperature	T_J	200	°C

Table 2. Thermal Characteristics

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction to Case	MRF373ALR1 MRF373ALSR1 $R_{\theta JC}$	0.89 0.63	°C/W

Table 3. ESD Protection Characteristics

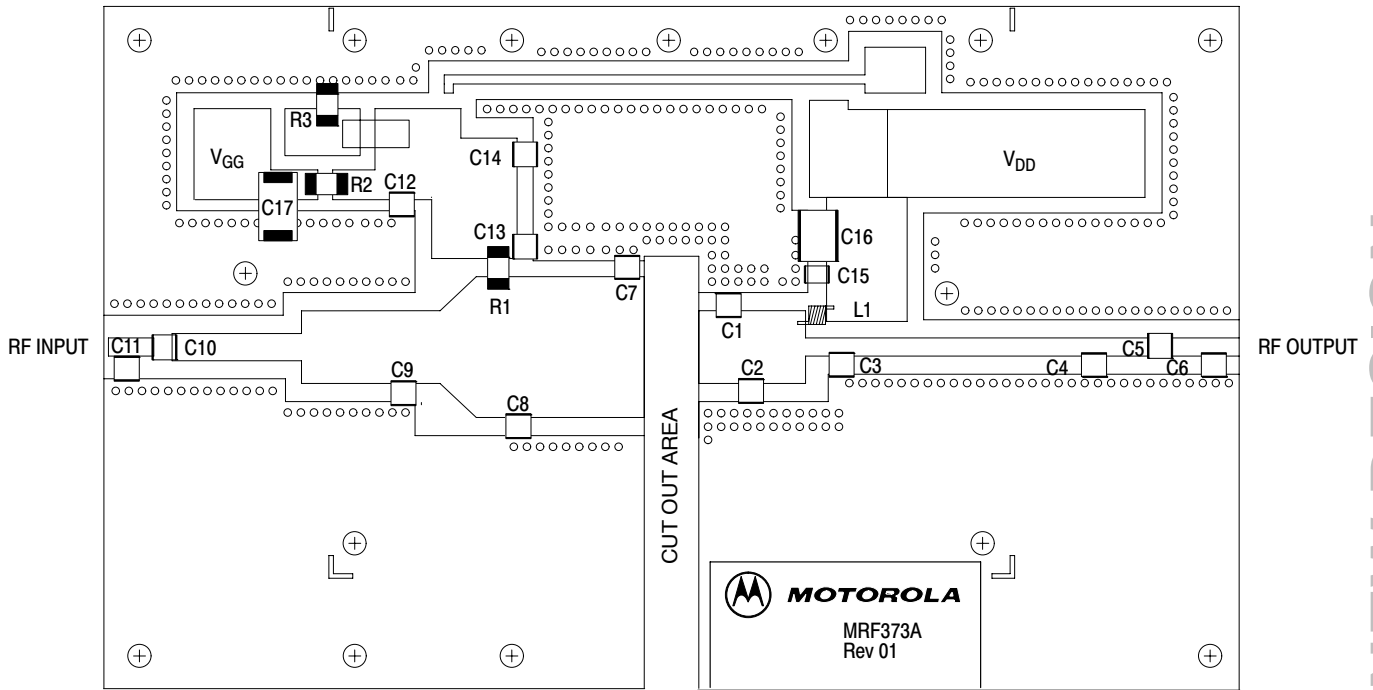
Test Conditions	Class
Human Body Model	1 (Minimum)
Machine Model	M2 (Minimum) M1 (Minimum)

Table 4. Electrical Characteristics ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
Off Characteristics					
Drain-Source Breakdown Voltage ($V_{GS} = 0\text{ Vdc}$, $I_D = 1\ \mu\text{A}$)	$V_{(BR)DSS}$	70	—	—	Vdc
Zero Gate Voltage Drain Current ($V_{DS} = 32\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$)	I_{DSS}	—	—	1	μAdc
Gate-Source Leakage Current ($V_{GS} = 5\text{ Vdc}$, $V_{DS} = 0\text{ Vdc}$)	I_{GSS}	—	—	1	μAdc
On Characteristics					
Gate Threshold Voltage ($V_{DS} = 10\text{ V}$, $I_D = 200\ \mu\text{A}$)	$V_{GS(th)}$	2	2.9	4	Vdc
Gate Quiescent Voltage ($V_{DS} = 32\text{ V}$, $I_D = 100\text{ mA}$)	$V_{GS(Q)}$	2.5	3.3	4.5	Vdc
Drain-Source On-Voltage ($V_{GS} = 10\text{ V}$, $I_D = 3\text{ A}$)	$V_{DS(on)}$	—	0.41	0.45	Vdc
Dynamic Characteristics					
Input Capacitance ($V_{DS} = 32\text{ V}$, $V_{GS} = 0$, $f = 1\text{ MHz}$)	C_{iss}	—	98.5	—	pF
Output Capacitance ($V_{DS} = 32\text{ V}$, $V_{GS} = 0$, $f = 1\text{ MHz}$)	C_{oss}	—	49	—	pF
Reverse Transfer Capacitance ($V_{DS} = 32\text{ V}$, $V_{GS} = 0$, $f = 1\text{ MHz}$)	C_{rss}	—	2	—	pF
Functional Characteristics (50 ohm system)					
Common Source Power Gain ($V_{DD} = 32\text{ V}$, $P_{out} = 75\text{ W CW}$, $I_{DQ} = 200\text{ mA}$, $f = 860\text{ MHz}$)	G_{ps}	16.5	18.2	—	dB
Drain Efficiency ($V_{DD} = 32\text{ V}$, $P_{out} = 75\text{ W CW}$, $I_{DQ} = 200\text{ mA}$, $f = 860\text{ MHz}$)	η	56	60	—	%

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Figure 1. MRF373ALR1/ALSR1 Narrowband Test Circuit Component Layout

Table 5. MRF373ALR1/ALSR1 Narrowband Test Circuit Component Layout Designations and Values

Designation	Description
C1, C2	18 pF Chip Capacitors
C3	12 pF Chip Capacitor
C4	1.8 pF Chip Capacitor
C5, C10	51 pF Chip Capacitors
C6	0.3 pF Chip Capacitor (Used only on the MRF373AS)
C7	15 pF Chip Capacitor
C8	10 pF Chip Capacitor
C9	2.7 pF Chip Capacitor
C11	0.5 pF Chip Capacitor
C12	1000 pF Chip Capacitor
C13	39 pF Chip Capacitor
C14, C15	470 pF Chip Capacitors
C16	2.2 μ F, 100 V Chip Capacitor
C17	10 μ F, 35 V Tantalum Capacitor
L1A	12 nH, Coilcraft
R1, R2	390 Ω , 1/2 W Chip Resistors (2010)
R3	1 k Ω , 1/2 W Chip Resistor (2010)
PCB	Arlon GX-0300-55, 30 mils, $\epsilon_r = 2.55$

TYPICAL CHARACTERISTICS

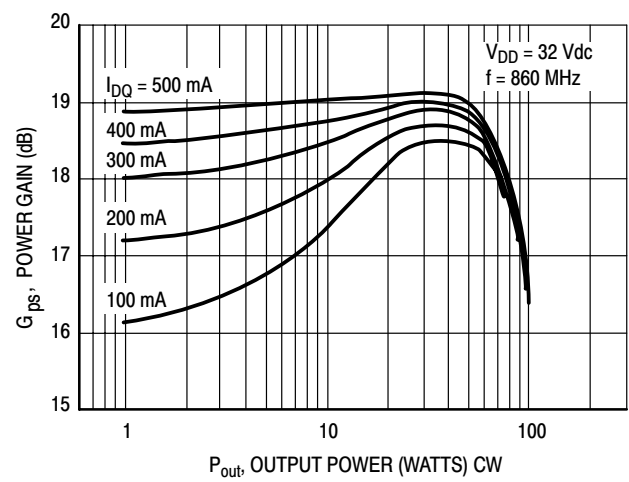


Figure 2. Power Gain versus Output Power

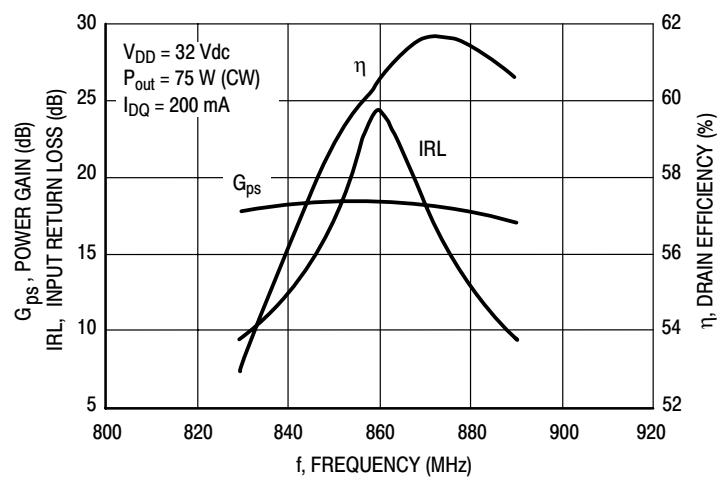


Figure 3. Performance in Narrowband Circuit

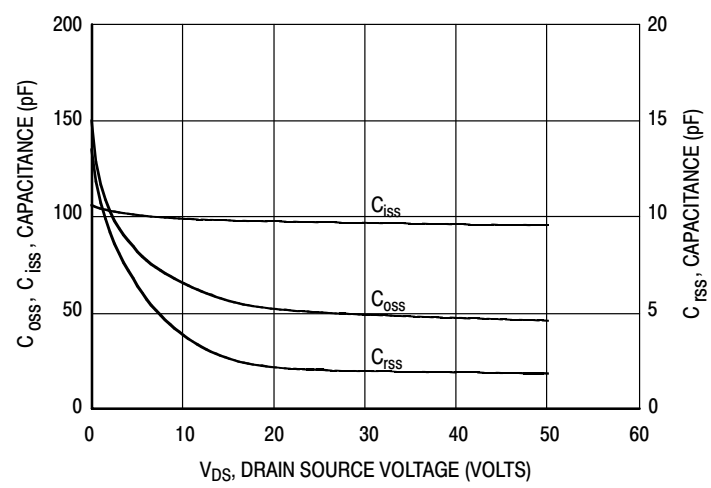
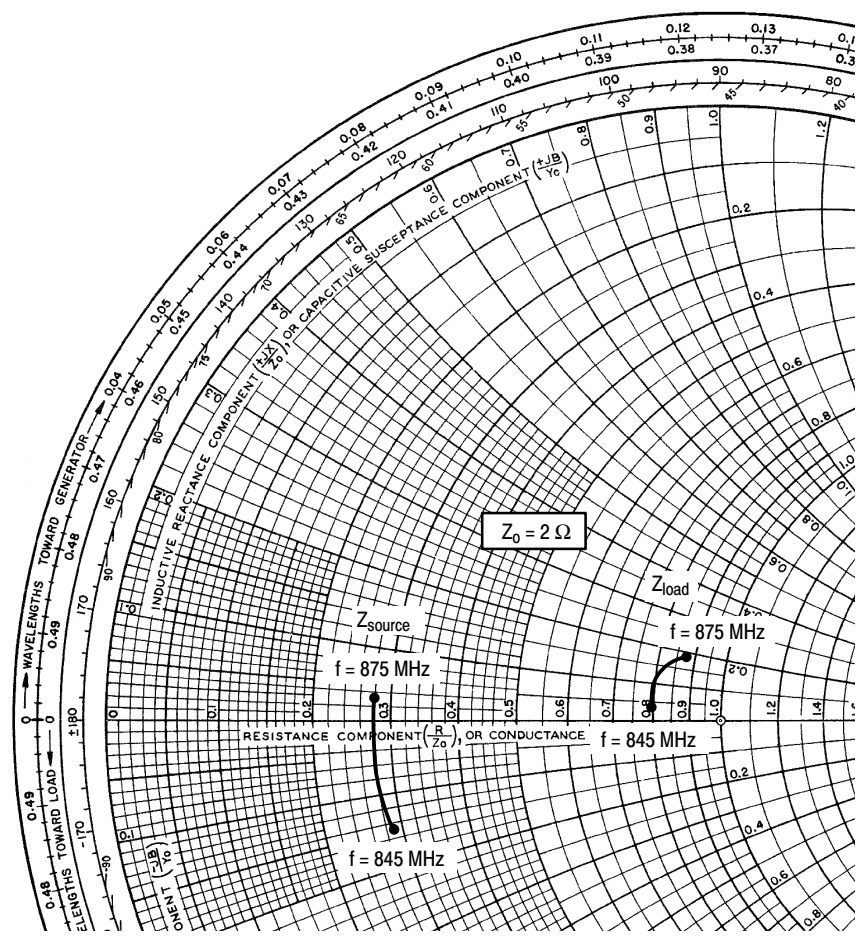


Figure 4. Capacitance versus Voltage



$V_{DD} = 32\text{ V}$, $I_{DQ} = 200\text{ mA}$, $P_{out} = 75\text{ W CW}$

f MHz	Z_{source} Ω	Z_{load} Ω
845	$0.58 - j0.29$	$1.60 + j0.07$
860	$0.56 - j0.11$	$1.65 + j0.22$
875	$0.56 + j0.06$	$1.79 + j0.38$

Z_{source} = Test circuit impedance as measured from gate to ground.

Z_{load} = Test circuit impedance as measured from drain to ground.

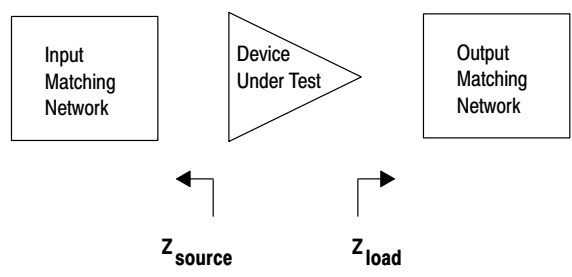
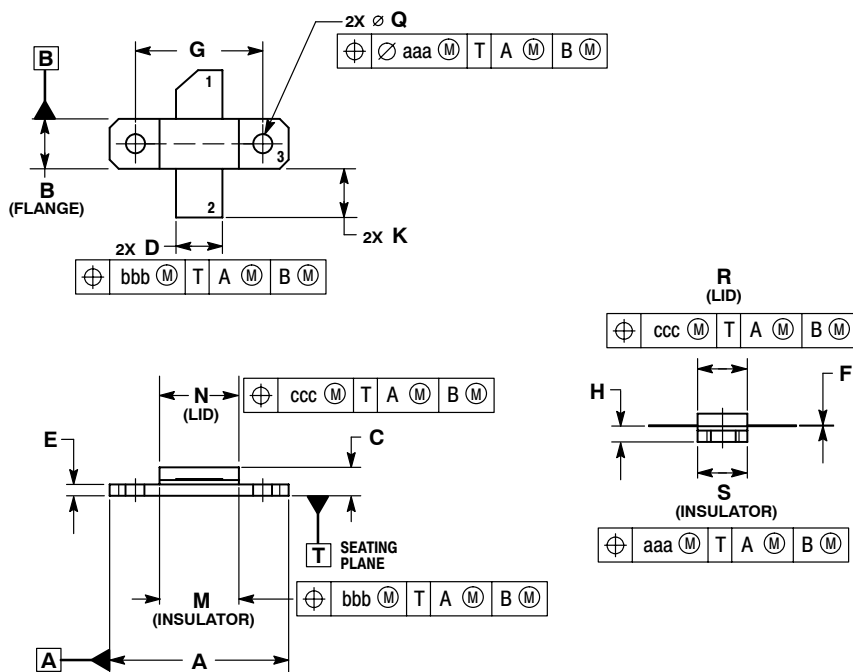


Figure 5. Series Equivalent Source and Load Impedance

PACKAGE DIMENSIONS



- NOTES:
1. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M-1994.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION H IS MEASURED 0.030 (0.762) AWAY FROM PACKAGE BODY.

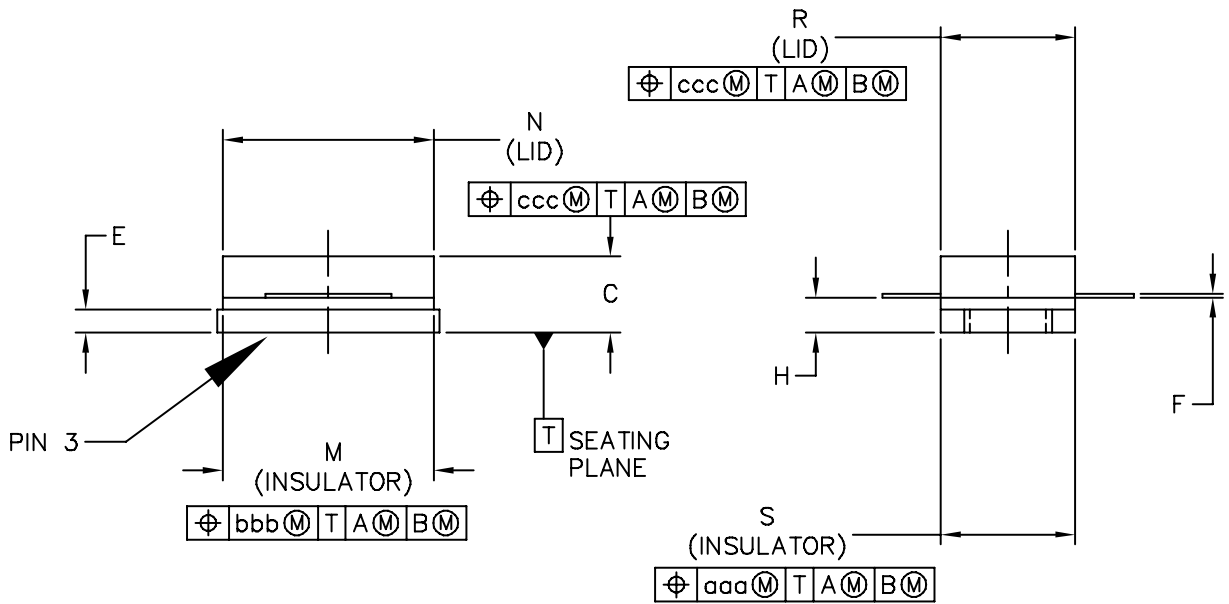
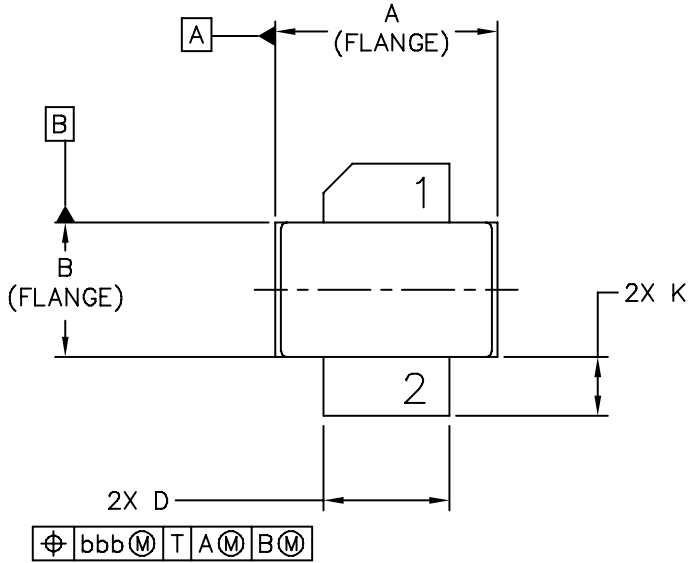
DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.795	0.805	20.19	20.45
B	0.225	0.235	5.72	5.97
C	0.125	0.175	3.18	4.45
D	0.210	0.220	5.33	5.59
E	0.055	0.065	1.40	1.65
F	0.004	0.006	0.10	0.15
G	0.562 BSC		14.28 BSC	
H	0.077	0.087	1.96	2.21
K	0.220	0.250	5.59	6.35
M	0.355	0.365	9.02	9.27
N	0.357	0.363	9.07	9.22
Q	0.125	0.135	3.18	3.43
R	0.227	0.233	5.77	5.92
S	0.225	0.235	5.72	5.97
aaa	0.005 REF		0.13 REF	
bbb	0.010 REF		0.25 REF	
ccc	0.015 REF		0.38 REF	

- STYLE 1:
 PIN 1. DRAIN
 2. GATE
 3. SOURCE

CASE 360B-05
 ISSUE G
 NI-360
 MRF373ALR1

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TITLE: NI-360S SURFACE MOUNT		DOCUMENT NO: 98ASB14516C		REV: F	
		CASE NUMBER: 360C-05		10 MAR 2006	
		STANDARD: NON-JEDEC			

NOTES:

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STYLE 1:

- PIN 1 - DRAIN
- 2 - GATE
- 3 - SOURCE

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DIM	INCH		MILLIMETER		DIM	INCH		MILLIMETER	
	MIN	MAX	MIN	MAX		MIN	MAX	MIN	MAX
A	.375	.385	9.53	9.78	N	.357	.363	9.07	9.22
B	.225	.235	5.72	5.97	R	.227	.233	5.77	5.92
C	.105	.155	2.67	3.94	S	.225	.235	5.72	5.97
D	.210	.220	5.33	5.59					
E	.035	.045	0.89	1.14	aaa	.005		0.13	
F	.004	.006	0.1	0.15	bbb	.010		0.25	
H	.057	.067	1.45	1.7	ccc	.015		0.38	
K	.085	.115	2.16	2.92					
M	.355	.365	9.02	9.27					

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		CASE NUMBER: 360C-05		10 MAR 2006	
		STANDARD: NON-JEDEC			

PRODUCT DOCUMENTATION

Refer to the following documents to aid your design process.

Engineering Bulletins

- EB212: Using Data Sheet Impedances for RF LDMOS Devices

REVISION HISTORY

The following table summarizes revisions to this document.

Revision	Date	Description
7	Sept. 2008	<ul style="list-style-type: none"> • Replaced Case Outline 360C-05, Issue E with Issue F, p. 7-8. • Added Product Documentation and Revision History, p. 9

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